

In the Specification:

Please amend Paragraph 33 as follows:

The first step is to deposit hard mask film 208 as depicted in FIGS. 2a - 2b. Hard mask film 208 acts as an etch stop layer and will be used throughout the Fin fabrication process when needed. Moreover, as will be made clear, a portion of hard mask film 208 forms what may be the capacitive dielectric for a high-voltage decoupling capacitor of the invention. For the exemplary purposes of this disclosure, hard mask film 208 may be silicon dioxide (SiO_2) or silicon nitride (Si_3N_4). In FIGS. 2b, 3b, 4b, 5b, 6b, and 7b, the "thickness" direction is oriented from left to right (i.e., parallel to the top surface of the hard mask film 208) and the "height" direction is oriented upward or downward (i.e., perpendicular to the top surface of the hard mask film 208).